



Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BV_{CEO} > 60V
- I_C = 3A High Continuous Collector Current
- ICM up to 6A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage V_{CE(SAT)} < 300mV @ 1A
- Complementary PNP Type: DXT751Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

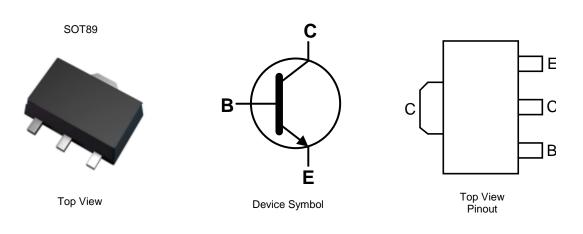
60V NPN LOW SATURATION POWER TRANSISTOR

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.052 grams (Approximate)

Applications

- Load Management Functions
- Motor Control
- DC-DC / DC-AC Converters



Ordering Information (Notes 4 and 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
DXT651Q-13	Automotive	KN2	13	12	2,500	

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

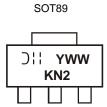
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \mathsf{KN2} = \mathsf{Product Type Marking Code} \\ \mathsf{O}^{\texttt{II}} = \mathsf{Manufacturer's Marking Code} \\ \mathsf{YWW} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Last Digit of Year (ex: 6 = 2016)} \\ \mathsf{WW} = \mathsf{Week Code (01 to 53)} \end{array}$



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3	А
Peak Pulse Collector Current	I _{CM}	6	A
Peak Base Current	Ι _Β	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

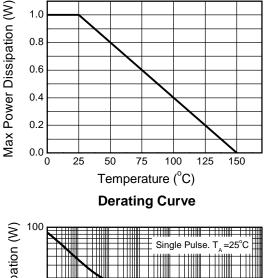
Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	D	1	W	
	(Note 7)	PD	2	vv	
Thermal Desistance Junction to Ambient Air	(Note 6)	P	125	00000	
Thermal Resistance, Junction to Ambient Air	(Note 7)	R _{0JA}	62.5	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		R _{θJL}	6.0	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

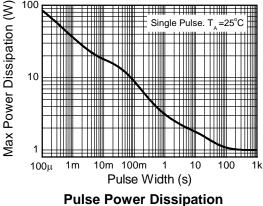
Notes: 6. For a device surface mounted on 15mm x 15mm x 0.6mm FR-4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.

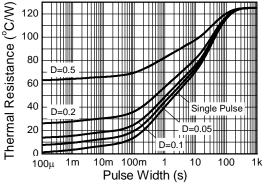
7. Same as note 6, except the device is mounted on 40mm x 40mm x 1.6mm FR-4 PCB.

8. Thermal resistance from junction to solder-point (on the exposed collector pad).

Thermal Characteristics and Derating Information







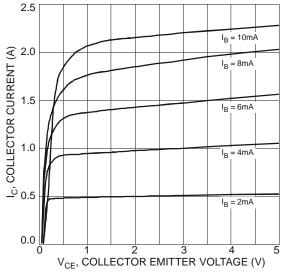




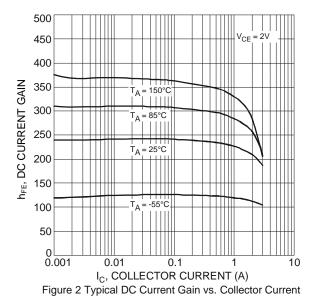
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						-
Collector-Base Breakdown Voltage	BV CBO	80			V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	60			V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_		0.1 10	μA	V _{CB} = 60V V _{CB} = 60V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	_	_	0.1	μA	$V_{EB} = 4V$
ON CHARACTERISTICS (Note 9)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.08 0.23	0.3 0.6	V V	$I_{C} = 1A, I_{B} = 100mA$ $I_{C} = 3A, I_{B} = 300mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	0.85	1.25	V	I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.8	1	V	$V_{CE} = 2V, I_C = 1A$
DC Current Gain	h _{FE}	70 100 80 40	200 200 185 120	 300 	_	$V_{CE} = 2V, I_C = 50mA$ $V_{CE} = 2V, I_C = 500mA$ $V_{CE} = 2V, I_C = 1A$ $V_{CE} = 2V, I_C = 2A$
SMALL-SIGNAL CHARACTERISTICS						
Transition Frequency	fT	140	200		MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{obo}	_		30	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{ON} t _{OFF}		35 230		ns ns	$V_{CC} = 10V. I_C = 500mA,$ $I_{B1} = -I_{B2} = 50mA$

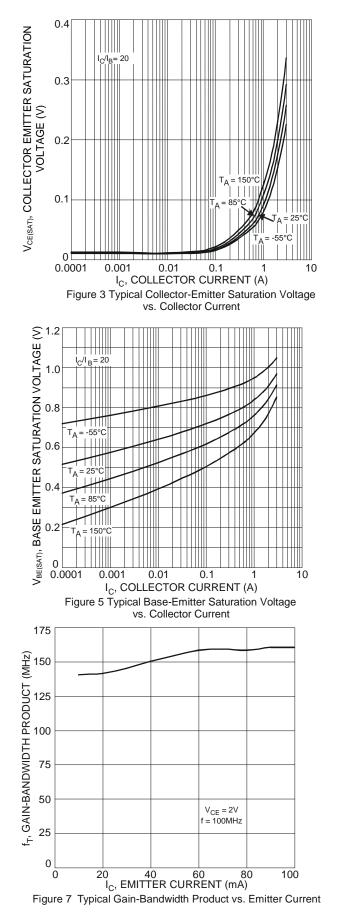
Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

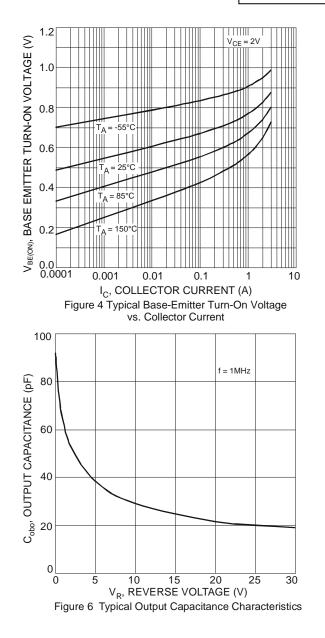










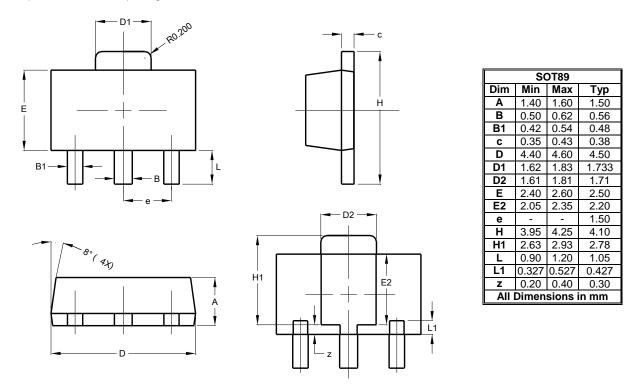




DXT651Q

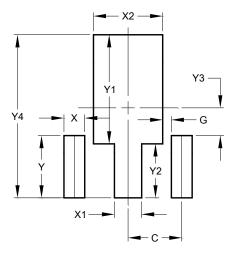
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
Dimensions				
С	1.500			
G	0.244			
Х	0.580			
X1	0.760			
X2	1.933			
Y	1.730			
Y1	3.030			
Y2	1.500			
Y3	0.770			
Y4	4.530			



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